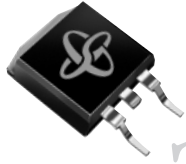
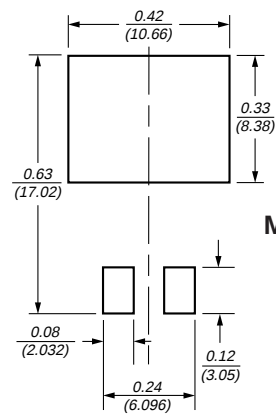
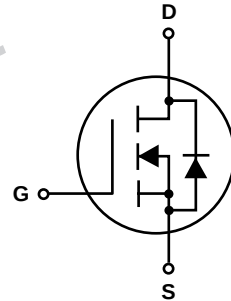
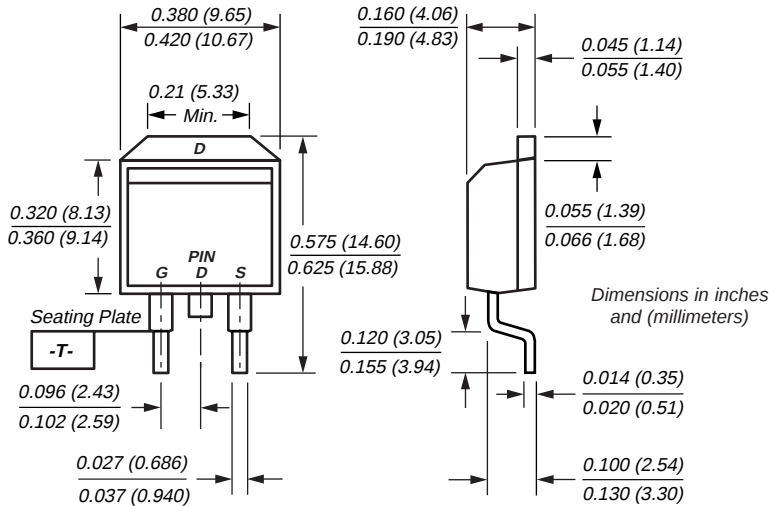


N-Channel Enhancement-Mode MOSFET
 V_{DS} 30V $R_{DS(ON)}$ 6.5m Ω I_D 80A

**TRENCH
GENFET®**
New Product
TO-263AB

**Mounting Pad
Layout**
Mechanical Data
Case: JEDEC TO-263 molded plastic body

Terminals: Leads solderable per MIL-STD-750, Method 2026

High temperature soldering guaranteed:
250°C/10 seconds at terminals

Mounting Position: Any **Weight:** 1.3g

Features

- Advanced Trench Process Technology
- High Density Cell Design for Ultra Low On-Resistance
- Specially Designed for Low Voltage DC/DC Converters
- Fast Switching for High Efficiency

Maximum Ratings and Thermal Characteristics ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ⁽¹⁾	I_D	80	A
Pulsed Drain Current	I_{DM}	240	
Maximum Power Dissipation $T_A = 25^\circ\text{C}$ $T_A = 100^\circ\text{C}$	P_D	69.4 27.8	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 150	$^\circ\text{C}$
Lead Temperature (1/8" from case for 5 sec.)	T_L	275	$^\circ\text{C}$
Junction-to-Case Thermal Resistance	$R_{\theta JC}$	1.8	$^\circ\text{C/W}$
Junction-to-Ambient Thermal Resistance ⁽²⁾	$R_{\theta JA}$	40	$^\circ\text{C/W}$

Notes: (1) Maximum DC current limited by the package

(2) 1-in² 2oz. Cu PCB mounted

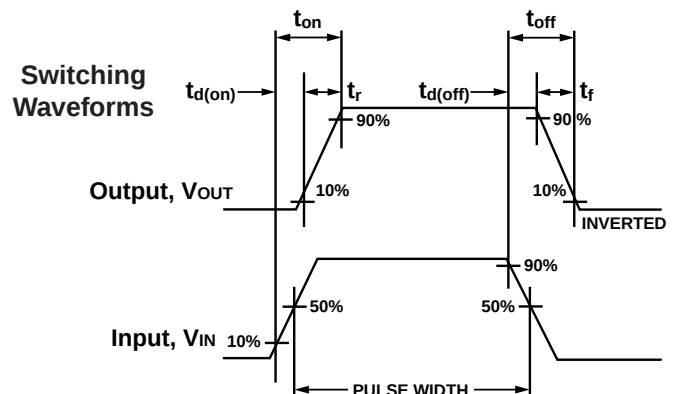
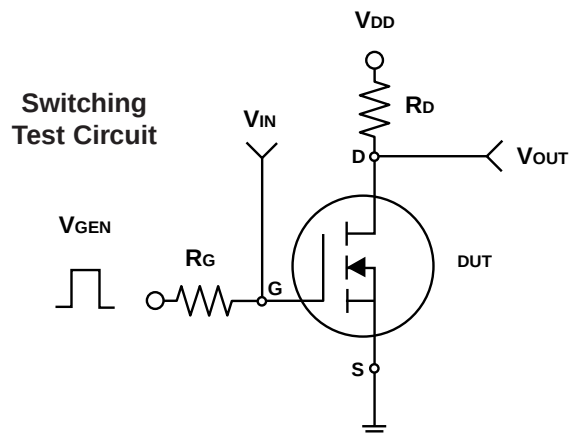
N-Channel Enhancement-Mode MOSFET

Electrical Characteristics (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D = 250μA	30	—	—	V
Drain-Source On-State Resistance ⁽¹⁾	R _{DS(on)}	V _{GS} = 10V, I _D = 38A	—	5.8	6.5	mΩ
		V _{GS} = 4.5V, I _D = 31A	—	8.5	9.5	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1.0	—	3.0	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30V, V _{GS} = 0V	—	—	1.0	μA
Gate-Body Leakage	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V	—	—	±100	nA
On-State Drain Current ⁽¹⁾	I _{D(on)}	V _{DS} ≥ 5V, V _{GS} = 10V	75	—	—	A
Forward Transconductance ⁽¹⁾	g _{fs}	V _{DS} = 15V, I _D = 38A	—	61	—	S
Dynamic						
Total Gate Charge	Q _g	V _{DS} =15V, I _D =38A, V _{GS} =5V	—	32.5	46	nC
Gate-Source Charge		V _{DS} = 15V, V _{GS} = 10V I _D = 38A	—	63	90	
Gate-Drain Charge	Q _{gd}		—	11	—	
Turn-On Delay Time	t _{d(on)}	V _{DD} = 15V, R _L = 15Ω I _D ≅ 1A, V _{GEN} = 10V R _G = 6Ω	—	13	26	ns
Turn-On Rise Time	t _r		—	16	29	
Turn-Off Delay Time	t _{d(off)}		—	94	132	
Turn-Off Fall Time	t _f		—	38	57	
Input Capacitance	C _{iss}	V _{DS} = 15V, V _{GS} = 0V f = 1.0MHz	—	3240	—	pF
Output Capacitance	C _{oss}		—	625	—	
Reverse Transfer Capacitance	C _{rss}		—	285	—	
Source-Drain Diode						
Max. Diode Forward Current	I _S	—	—	—	75	A
Diode Forward Voltage	V _{SD}	I _S = 38A, V _{GS} = 0V	—	0.9	1.3	V

Note:

(1) Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%



N-Channel Enhancement-Mode MOSFET

Ratings and Characteristic Curves ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Fig. 1 – Output Characteristics

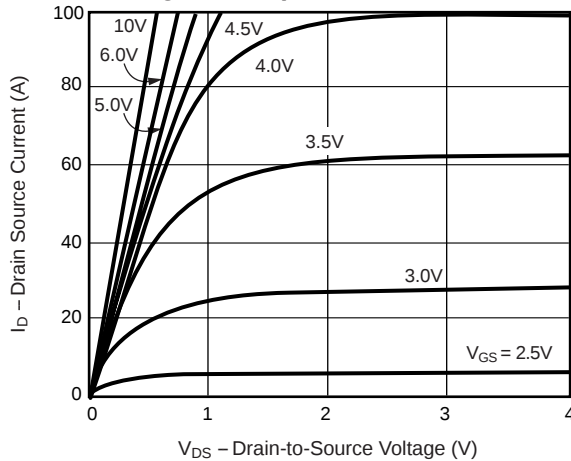


Fig. 2 – Transfer Characteristics

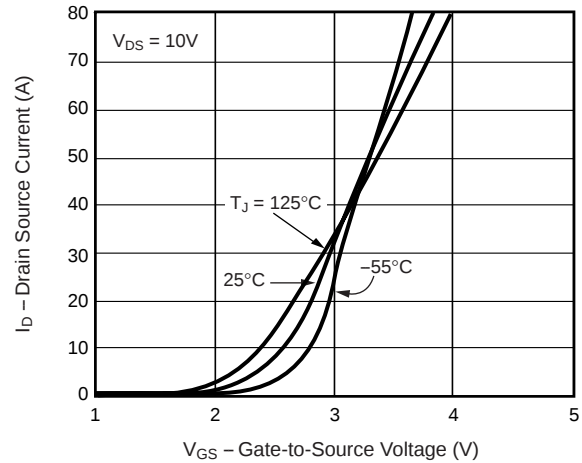


Fig. 3 – Threshold Voltage vs. Temperature

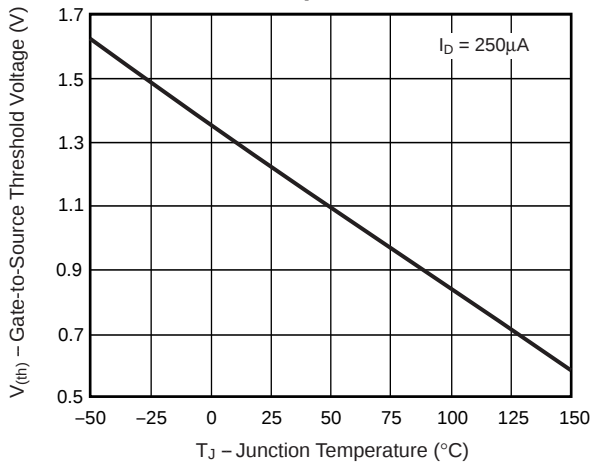


Fig. 4 – On-Resistance vs. Drain Current

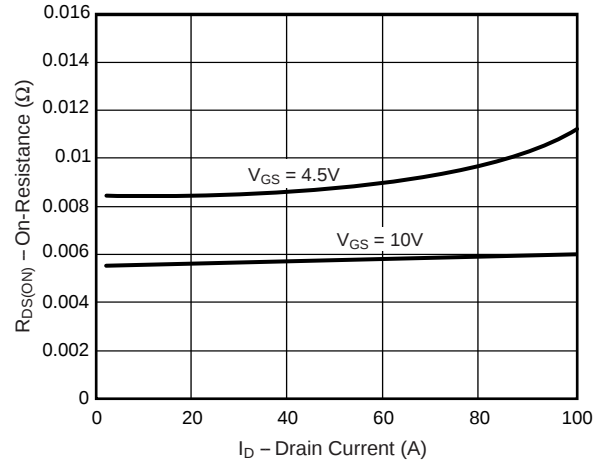
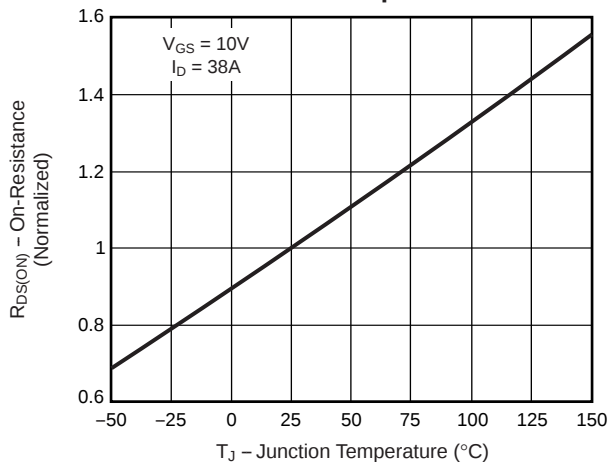


Fig. 5 – On-Resistance vs. Junction Temperature



N-Channel Enhancement-Mode MOSFET

Ratings and Characteristic Curves ($T_A = 25^\circ\text{C}$ unless otherwise noted)

**Fig. 6 – On-Resistance vs.
Gate-to-Source Voltage**

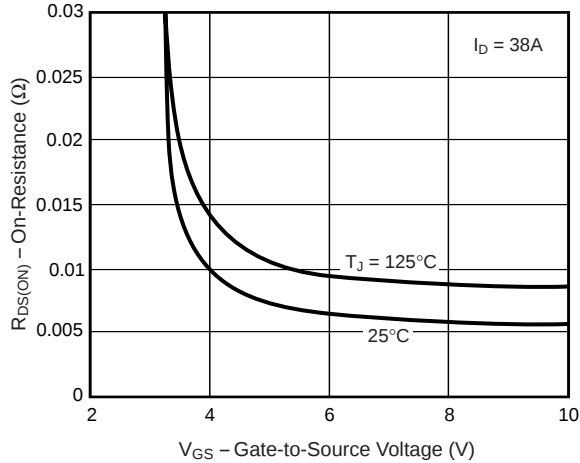


Fig. 7 – Gate Charge

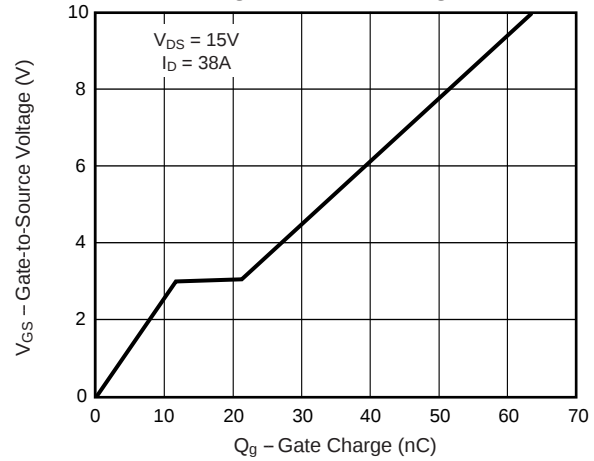
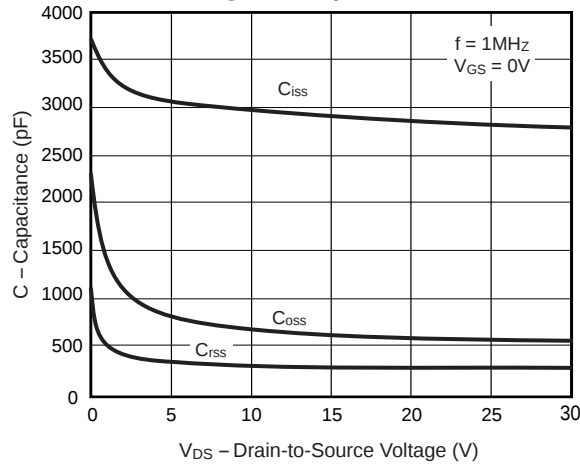
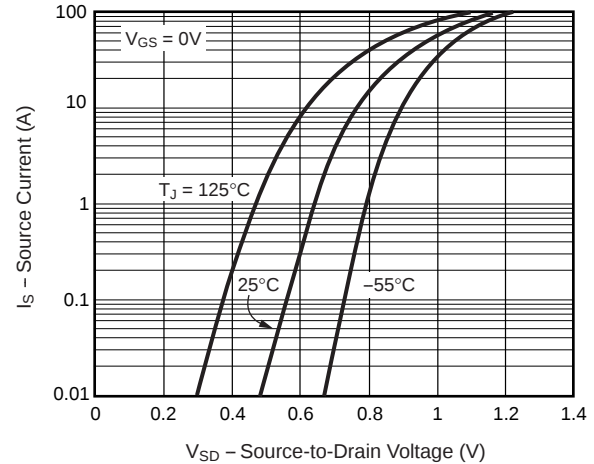


Fig. 8 – Capacitance



**Fig. 9 – Source-Drain Diode
Forward Voltage**



N-Channel Enhancement-Mode MOSFET

Ratings and Characteristic Curves ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Fig. 10 – Breakdown Voltage vs. Junction Temperature

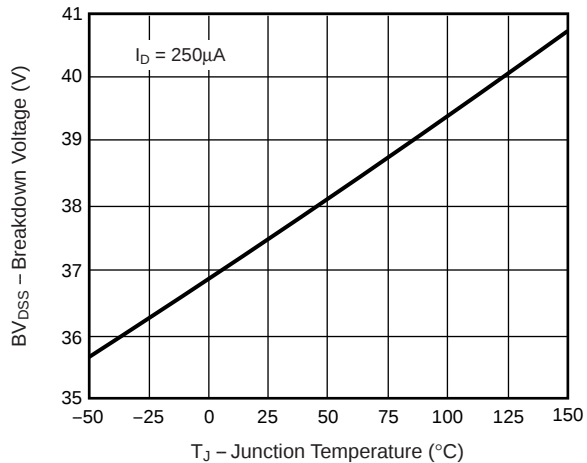


Fig. 11 – Transient Thermal Impedance

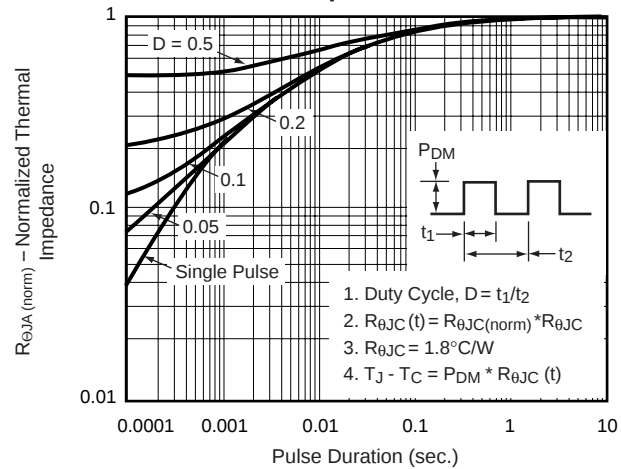


Fig. 12 – Power vs. Pulse Duration

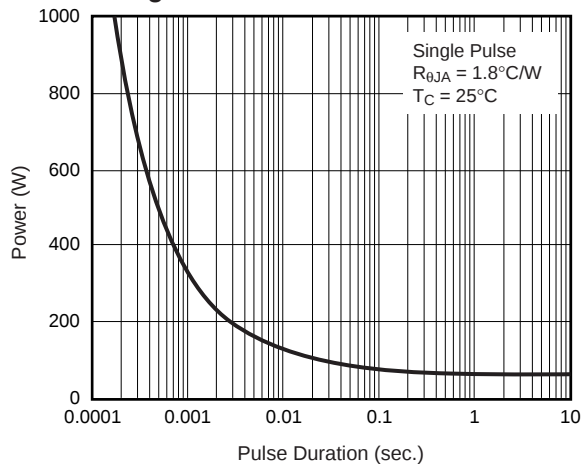


Fig. 13 – Maximum Safe Operating Area

